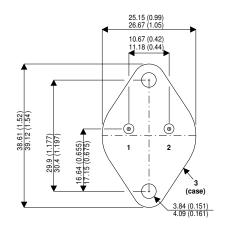
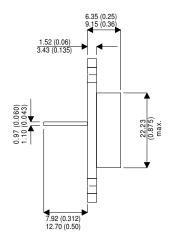


BDY25A

MECHANICAL DATA

Dimensions in mm (inches)





HIGH CURRENT NPN SILICON TRANSISTOR

FEATURES

- HIGH CURRENT FAST SWITCHING
- HIGH RELIABILITY
- SCREENING OPTIONS AVAILABLE

APPLICATIONS

- SWITCHING CIRCUITS
- LARGE SIGNAL/POWER AMPLIFIERS

TO3 (TO204AA)

Pin 1 = Base Pin 2 = Emitter Case = Collector

ABSOLUTE MAXIMUM RATINGS

$T_{CASE} = 2$	$5^{\circ}\!$		
V_{CBO}	Collector - Base Voltage		200V
$V_{\sf CEO}$	Collector - Emitter Voltage		140V
V_{EBO}	Emitter – Base Voltage	10V	
I_{C}	Continuous Collector Current		6A
I_{B}	Base Current		3A
P_{tot}	Total Power Dissipation at	$T_{case} = 25$ °C	50W
		Derate above 25 ℃	0.29 W/℃
T_J	Junction Temperature		200℃
T_{stg}	Storage Temperature		-65 to 200 ℃

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BDY25A

THERMAL CHARACTERISTICS	Max	Unit
R _{th} j-case Thermal resistance to case	3.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case}=25 °C unless otherwise stated)

	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-Off Current	V _{CE} = 140V	$I_B = 0$			1.0	
I _{CES}	Collector Cut-Off Current	V _{CE} = 180V	V _{BE} = 0			1.0	mA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 10V	I _C = 0			1.0	
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage	$I_C = 50mA$	I _B = 0	140			
V _{(BR)CBO} *	Collector-Base Breakdown Voltage	$I_C = 3mA$		200			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 2.0A	$I_B = 0.25A$			0.6	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 2.0A	$I_{B} = 0.25A$			1.2	
h _{FE} *	Forward-current transfer ratio	I _C = 1.0A	V _{CE} = 4.0V		55		
		I _C = 2.0A	V _{CE} = 4.0V	15	20	45	

DYNAMIC CHARACTERISTICS

C _{obo}	Output Capacitance	$I_E = 0$ $f = 1.0MHz$	V _{CB} = 10V		65	120	pF
F _T	Transition Frequency	$I_C = 0.5A$ f = 10.0MHz	V _{CE} = 15V	10			MHz
T _{on}	Turn-on time	I _C = 5.0A	I _{B1} = 1.0A		0.3	0.5	20
T _{off}	Turn-off time	I _C = 5.0A	$I_{B1} = -I_{B2} = 1.0A$		1.5	2.0	μs

^{*} Pulse test t_p = 300 μ s, δ < 2%

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